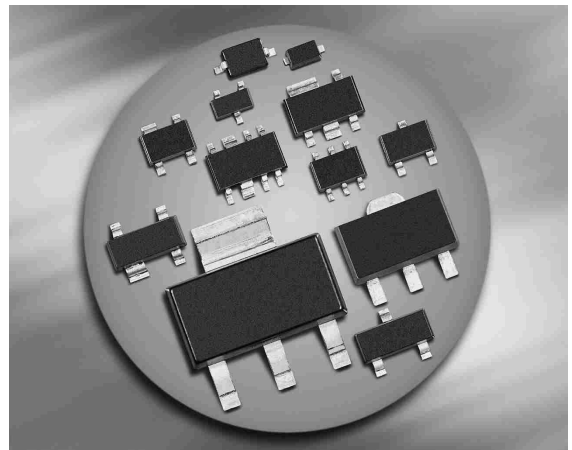


Silicon Tuning Diode

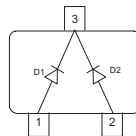
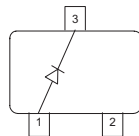
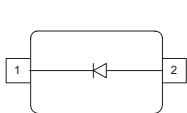
- High Q hyperabrupt tuning diode
- Designed for low tuning voltage operation for VCO's in mobile communications equipment
- High ratio at low reverse voltage



BBY53-02L
BBY53-02V
BBY53-02W
BBY53-03W

BBY53-03L

BBY53
BBY53-05W



Type	Package	Configuration	L_S (nH)	Marking
BBY53	SOT23	common cathode	2	S7s
BBY53-02L *	TSLP-2-1	single, leadless	0.4	LL
BBY53-02V	SC79	single	0.6	L
BBY53-02W	SCD80	single	0.6	LL
BBY53-03L *	TSLP-3-1	single, leadless	0.4	LL
BBY53-03W	SOD323	single	1.8	white/5
BBY53-05W	SOT323	common cathode	1.4	S7s

* Preliminary

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

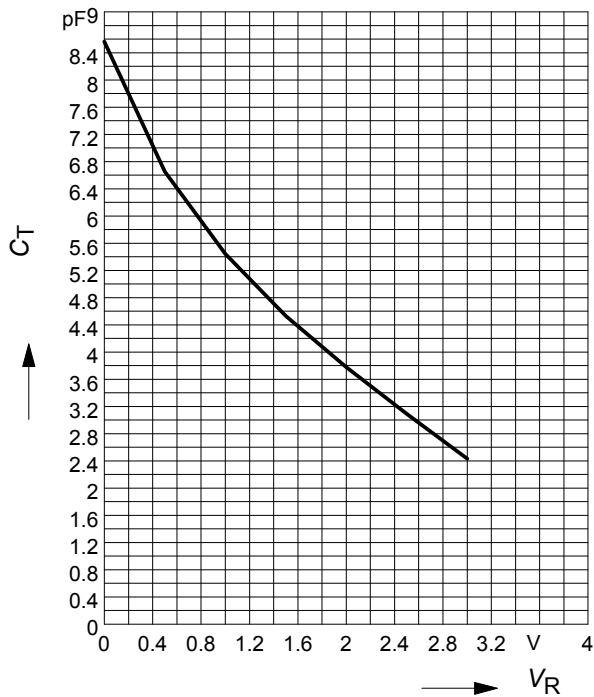
Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	6	V
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ... 125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ... 150	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current $V_R = 4\text{ V}$ $V_R = 4\text{ V}, T_A = 85\text{ }^{\circ}\text{C}$	I_R	- - -	- - -	10 200	nA
AC Characteristics					
Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$ $V_R = 3\text{ V}, f = 1\text{ MHz}$	C_T	4.8 1.85	5.3 2.4	5.8 3.1	pF
Capacitance ratio $V_R = 1\text{ V}, V_R = 3\text{ V}, f = 1\text{ MHz}$	C_{T1}/C_{T3}	1.8	2.2	2.6	
Series resistance $V_R = 1\text{ V}, f = 1\text{ GHz}$	r_S	-	0.47	-	Ω

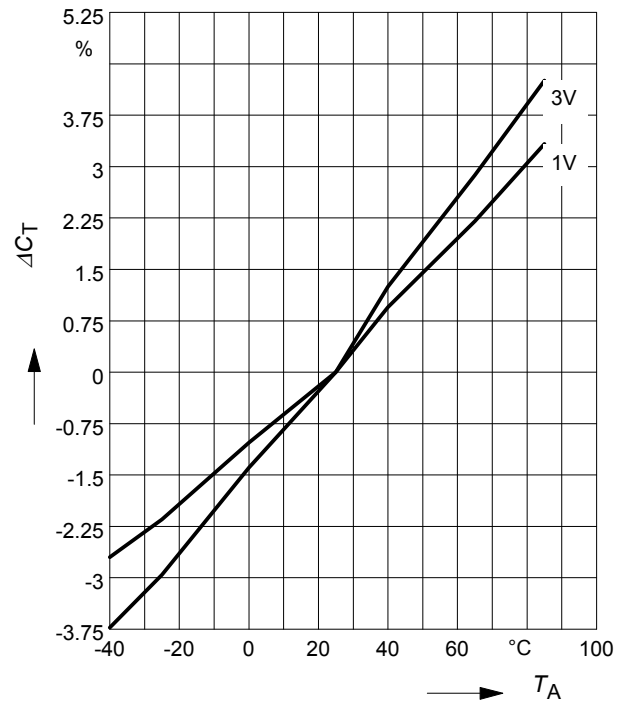
Diode capacitance $C_T = f(V_R)$

$f = 1\text{ MHz}$



Capacitance change $\Delta C = f(T_A)$

$f = 1\text{ MHz}$



Temperature coefficient of the diode capacitance $TC_C = f(V_R)$

$f = 1\text{ MHz}$

